Amendments to the Claims

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

- 1. (original) A sensor comprising:
 - a substrate;
 - a pixel situated on a single level on the substrate; and an electronics circuit situated on the single level.
- 2. (original) The sensor of claim 1, wherein the pixel has a fill factor greater than 69 percent.
- 3. (original) The sensor of claim 2, wherein the pixel is an infrared light detector.
- 4. (original) The sensor of claim 3, wherein the substrate has a pit proximate to the pixel.
- 5. (original) The sensor of claim 4, wherein the pixel has at least one via in the one level supporting the pixel.
- 6. (original) The sensor of claim 5, wherein the electronics circuit comprises a FET circuit.
- 7. (original) The sensor of claim 5, wherein the electronics comprises a bipolar transistor circuit.
- 8. (currently amended) The sensor of claim 6, wherein the electronics circuit comprises at least one small area FET, leaving a significant portion of the substrate free of circuits.

 2 of 10

- 9. (original) The sensor of claim 8, wherein the electronics is CMOS circuitry.
- 10. (original) The sensor of claim 9, wherein the pixel is a microbolometer.
- 11. (original) A thermal sensor comprising:

a substrate; and

an array of pixels situated on the substrate; and

wherein:

each pixel is located on a single level;

an electronic circuit is associated with each pixel; and

each electronic circuit is located on the single level with the pixel.

- 12. (original) The sensor of claim 11, wherein each pixel is an infrared light detector.
- 13. (original) The sensor of claim 12, wherein each pixel is suspended over a pit in the substrate.
- 14. (original) The sensor of claim 13, wherein each electronic circuit is CMOS FET circuitry.
- 15. (original) The sensor of claim 14, wherein each pixel is a microbolometer.
- 16. (original) A sensing means comprising:

means for sensing infrared light;

means for electronically processing signals related to infrared light sensed by the means for sensing infrared light; and

3 of 10

means for supporting on one level the means for sensing infrared light and the means for electronically processing signals.

- 17. (original) The means of claim 16, wherein the means for supporting on one level supports the means for sensing infrared light over a thermal isolating opening.
- 18. (original) The means of claim 17, wherein the means for electronically processing signals has an area that is a fraction of the area of the means for sensing infrared light.
- 19. (original) The means of claim 18, wherein the means for sensing infrared light is an array of pixels.
- 20. (currently amended) The means of claim 19, wherein:
 each pixel of the array of pixels is a microbolometer pixel comprising VO_x; and the means for electronically processing signals is small area transistor circuitry that leaves a significant portion of the means for supporting free of circuits.
- 21. (original) The means of claim 20, wherein the small area transistor circuitry is CMOS FET circuitry.
- 22. (original) The means of claim 21, wherein:

 the means for supporting on one level is a planar level substrate; and
 the thermal isolating opening is a pit in the substrate under each pixel of the array
 of pixels.
- (original) A sensor comprising:
 a substrate;

4 of 10

a pixel situated in a first plane relative to a surface of the substrate; and an electronics circuit situated in the first plane.

24. (original) A thermal sensor comprising:

a substrate; and

an array of pixels situated on the substrate; and

wherein:

each pixel is located on a first surface;

an electronic circuit is associated with each pixel; and

each electronic circuit is located on the first surface proximate to the pixel.

25. (original) A thermal sensor comprising:

a substrate; and

an array of pixels situated on the substrate; and

wherein:

an electronic circuit is associated with each pixel; and

each electronic circuit is situated horizontally proximate to the pixel.

26. (original) A thermal sensor comprising:

a substrate; and

an array of pixels situated on the substrate; and

electronics situated on the substrate horizontally proximate to the array of pixels.

27. (original) A sensing means comprising:

means for sensing infrared light;

means for electronically processing signals related to infrared light sensed by the means for sensing infrared light; and

5 of 10

means for supporting on one surface the means for sensing infrared light and the means for electronically processing signals.

28. (original) A sensing means comprising:

means for sensing infrared light;

means for electronically processing signals related to infrared light sensed by the means for sensing infrared light; and

means for supporting the means for sensing infrared light and the means for electronically processing signals horizontally proximate to each other.

29. (original) A sensing means comprising:

means for sensing infrared light;

means for electronically processing signals related to infrared light sensed by the means for sensing infrared light; and

means for supporting in a plane the means for sensing infrared light and the means for electronically processing signals.